

# FDP6670AL/FDB6670AL

## N-Channel Logic Level PowerTrench<sup>®</sup> MOSFET

### General Description

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

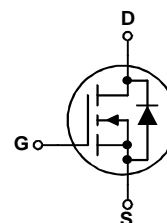
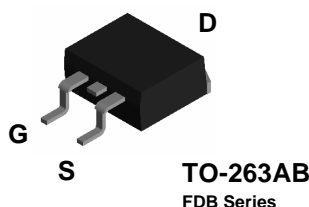
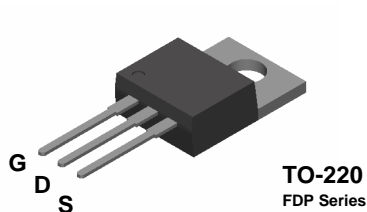
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{DS(ON)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

It has been optimized for low gate charge, low  $R_{DS(ON)}$  and fast switching speed.

### Features

- 80 A, 30 V  $R_{DS(ON)} = 6.5 \text{ m}\Omega$  @  $V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 8.5 \text{ m}\Omega$  @  $V_{GS} = 4.5 \text{ V}$
- Critical DC electrical parameters specified at elevated temperature
- High performance trench technology for extremely low  $R_{DS(ON)}$
- 175°C maximum junction temperature rating



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous (Note 1)	80	A
	– Pulsed (Note 1)	240	
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	68	W
	Derate above $25^\circ\text{C}$	0.45	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	$-65$ to $+175$	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDB6670AL	FDB6670AL	13"	24mm	800 units
FDP6670AL	FDP6670AL	Tube	n/a	45

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 1)						
$W_{DSS}$	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 15\text{ V}, I_D = 80\text{ A}$			114	mJ
$I_{AR}$	Maximum Drain-Source Avalanche Current				80	A
Off Characteristics						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$		24		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 40\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 37\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 40\text{ A}, T_J = 125^\circ\text{C}$		5.2 6.5 7.2	6.5 8.5 9.7	m $\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 10\text{ V}$	80			A
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{V}, I_D = 40\text{ A}$		115		S
Dynamic Characteristics						
$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		2440		pF
$C_{oss}$	Output Capacitance			580		pF
$C_{rss}$	Reverse Transfer Capacitance			250		pF
$R_G$	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		1.4		$\Omega$
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10\text{V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		13	23	ns
$t_r$	Turn-On Rise Time			13	23	ns
$t_{d(off)}$	Turn-Off Delay Time			42	68	ns
$t_f$	Turn-Off Fall Time			15	27	ns
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 40\text{ A},$ $V_{GS} = 5\text{ V}$		24	33	nC
$Q_{gs}$	Gate-Source Charge			7		nC
$Q_{gd}$	Gate-Drain Charge			9		nC
Drain-Source Diode Characteristics and Maximum Ratings						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current				80	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 40\text{ A}$ (Note 1)		0.9	1.3	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 40\text{ A},$		34		nS
$Q_{rr}$	Diode Reverse Recovery Charge	$dI_F/dt = 100\text{ A}/\mu\text{s}$		24		nC

**Notes:**1. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%

## Typical Characteristics

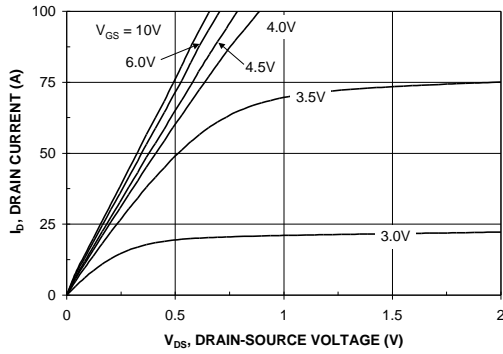


Figure 1. On-Region Characteristics.

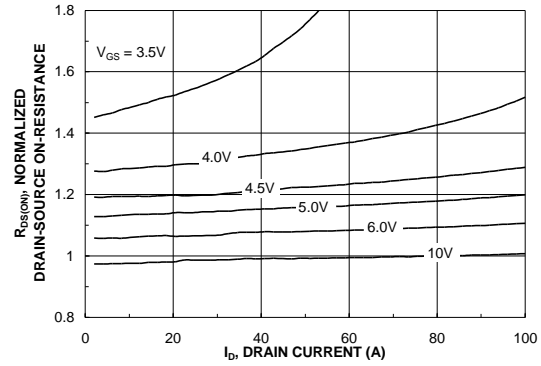


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

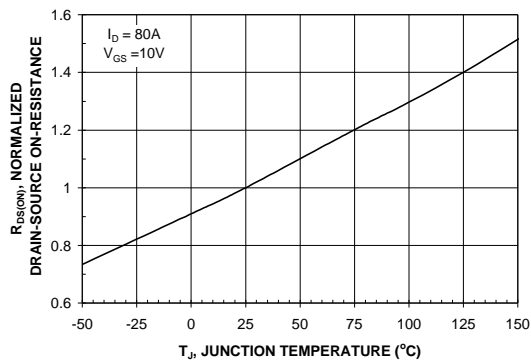


Figure 3. On-Resistance Variation with Temperature.

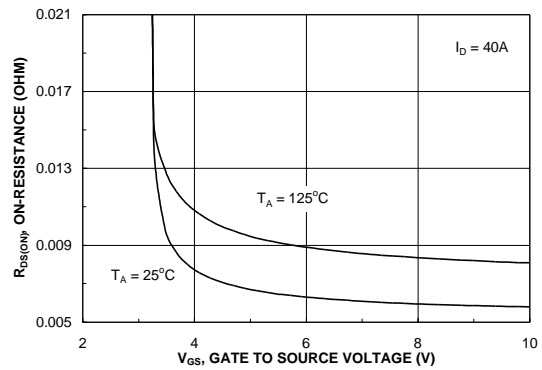


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

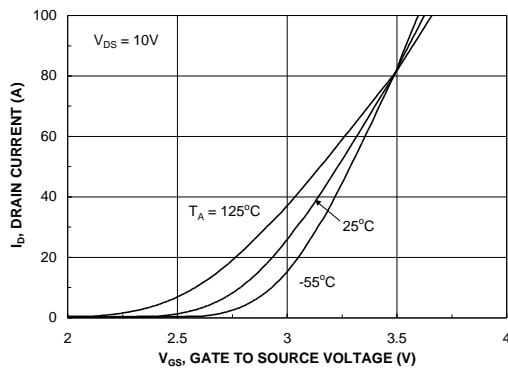


Figure 5. Transfer Characteristics.

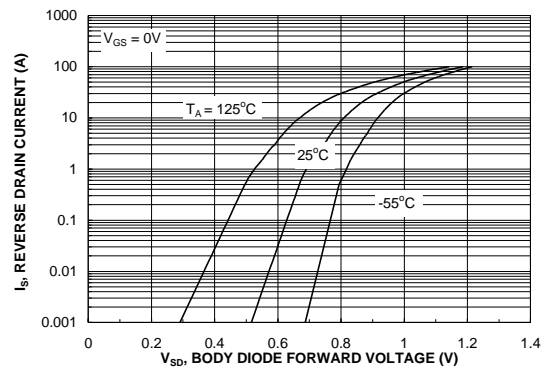


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

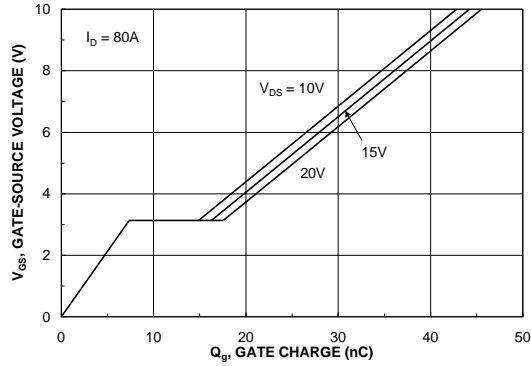


Figure 7. Gate Charge Characteristics.

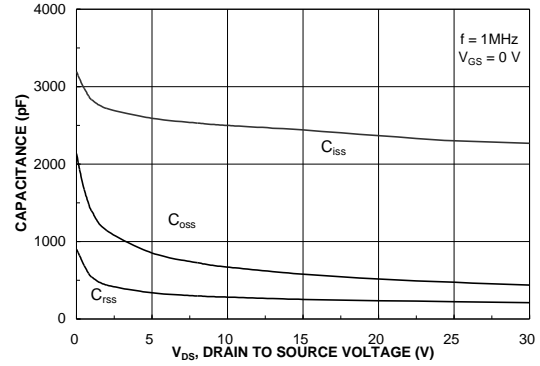


Figure 8. Capacitance Characteristics.

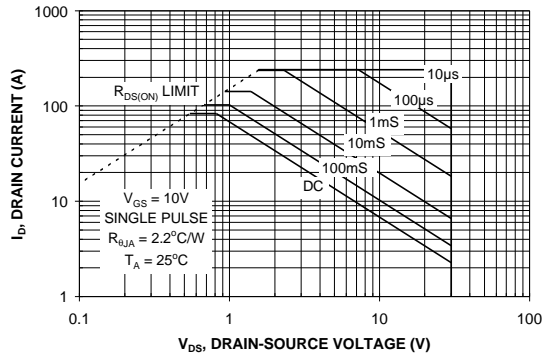


Figure 9. Maximum Safe Operating Area.

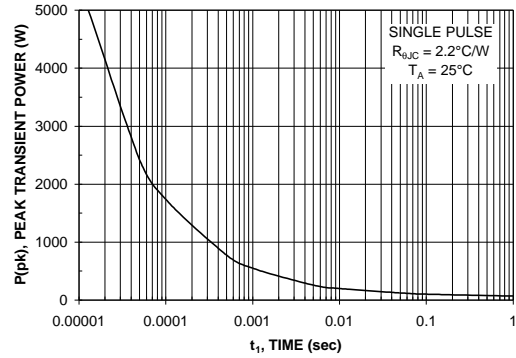


Figure 10. Single Pulse Maximum Power Dissipation.

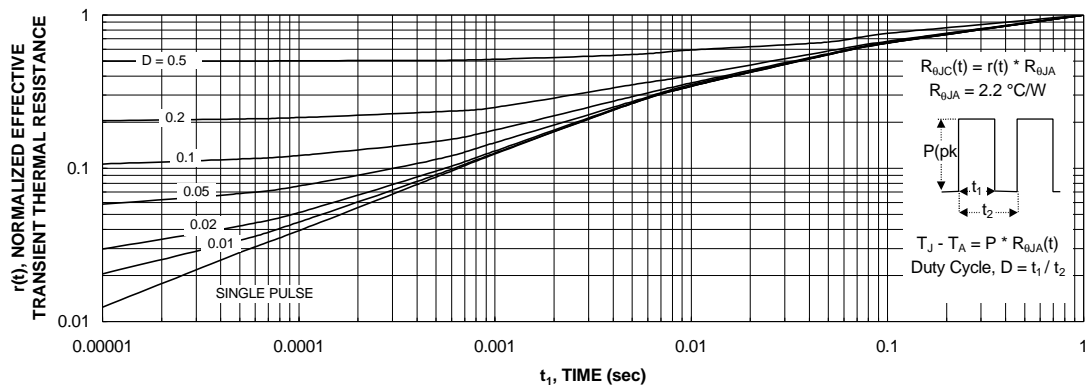


Figure 11. Transient Thermal Response Curve.

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